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BDC04

CASE 29-03, STYLE 14
TO-92 (TO-226AE)

ONE WATT
AMPLIFIER TRANSISTOR

PNP SILICON

Refer to MPSW51 for graphs.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	20	Vdc
Collector-Base Voltage	V_{CBO}	25	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	Vdc
Collector Current – Continuous	I_C	1.0	Adc
Total Device Dissipation @ T_A = 25°C Derate above 25°C	P_D	1.0 8.0	Watt mW/°C
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	2.5 20	Watt mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) (I_C = 10 mAdc, I_B = 0)	$V_{(BR)CEO}$	20	—	Vdc
Collector-Base Breakdown Voltage (I_C = 100 μAdc, I_E = 0)	$V_{(BR)CBO}$	25	—	Vdc
Emitter-Base Breakdown Voltage (I_E = 100 μAdc, I_C = 0)	$V_{(BR)EBO}$	5.0	—	Vdc
Collector Cutoff Current (V_{CB} = 25 Vdc, I_E = 0)	I_{CBO}	—	0.1	μAdc
Emitter Cutoff Current (V_{EB} = 5.0 Vdc, I_C = 0)	I_{EBO}	—	0.1	μAdc
ON CHARACTERISTICS (1)				
DC Current Gain (I_C = 500 mAdc, V_{CE} = 1 Vdc) (I_C = 5 mAdc, V_{CE} = 10 Vdc) (I_C = 1000 mAdc, V_{CE} = 1 Vdc)	h_{FE}	 85 50 60	 375 — —	—
Collector-Emitter Saturation Voltage (I_C = 1000 mAdc, I_B = 100 mAdc)	$V_{CE(sat)}$	—	0.7	Vdc
Base-Emitter On Voltage (I_C = 1000 mAdc, V_{CE} = 1.0 Vdc)	$V_{BE(on)}$	—	1.2	Vdc
DYNAMIC CHARACTERISTICS				
Current Gain–Bandwidth Product (I_C = 50 mAdc, V_{CE} = 10 Vdc, f = 20 MHz)	f_T	50	—	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f = 1.0 MHz)	C_{obo}	—	30	pF

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.